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HMC450* Product Page Quick Links

Last Content Update: 11/01/2016

Comparable Parts

View a parametric search of comparable parts

Evaluation Kits

- HMC450QS16G Evaluation Board

Documentation

Application Notes

- AN-1363: Meeting Biasing Requirements of Externally Biased RF/Microwave Amplifiers with Active Bias Controllers
- Broadband Biasing of Amplifiers General Application Note
- MMIC Amplifier Biasing Procedure Application Note
- Thermal Management for Surface Mount Components General Application Note

Data Sheet

- HMC450 Data Sheet

Tools and Simulations

- HMC450 S-Parameter

Reference Materials

Quality Documentation

- HMC Legacy PCN: QS##, QS##E and QS##G, QS##GE packages - Relocation of pre-existing production equipment to new building
- Package/Assembly Qualification Test Report: Plastic Encapsulated QSOP (QTR: 02015 REV: 11)
- Semiconductor Qualification Test Report: GaAs HBT-B (QTR: 2013-00229)

Design Resources

- HMC450 Material Declaration
- PCN-PDN Information
- Quality And Reliability
- Symbols and Footprints

Discussions

View all HMC450 EngineerZone Discussions

Sample and Buy

Visit the product page to see pricing options

Technical Support

Submit a technical question or find your regional support number

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Typical Applications

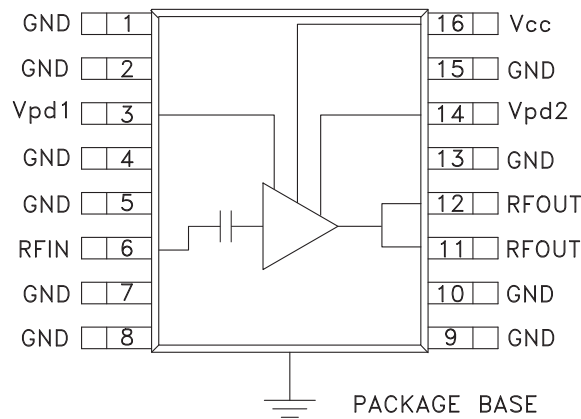
The HMC450QS16G / HMC450QS16GE is ideal for power and driver amplifier applications:

- GSM, GPRS, & Edge
- CDMA & WCDMA
- Base Stations & Repeaters

Features

- Gain: 26 dB
- 32% PAE @ 28.5 dBm Output Power
- +40 dBm Output IP3
- Integrated Power Control (Vpd)
- Included in the HMC-DK002 Designer's Kit

Functional Diagram



General Description

The HMC450QS16G & HMC450QS16GE are high efficiency GaAs InGaP HBT Medium Power MMIC amplifiers operating between 800 and 1000 MHz. The amplifier is packaged in a low cost, surface mount 16 lead package and offers the same pinout and functionality as the higher band HMC413QS16G 1.6-2.3 GHz PA. With a minimum of external components, the amplifier provides 26 dB of gain, +40 dBm OIP3 and +28.5 dBm of saturated power from a +5V supply voltage. The integrated power control (Vpd) can be used for full power down or RF output power/current control. The combination of high gain and high output IP3 make the HMC450QS16G & HMC450QS16GE ideal linear drivers for Cellular, PCS & 3G applications.

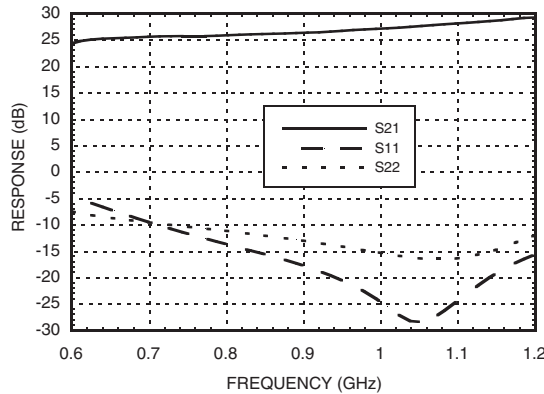
Electrical Specifications, $T_A = +25^\circ\text{C}$, $V_s = +5\text{V}$, $V_{pd} = +4\text{V}$ [1]

Parameter	Min.	Typ.	Max.	Units
Frequency Range	0.8 - 1.0			GHz
Gain	23	26		dB
Gain Variation Over Temperature		0.015	0.025	dB/°C
Input Return Loss		17		dB
Output Return Loss		13		dB
Output Power for 1 dB Compression (P1dB)	23	26		dBm
Saturated Output Power (Psat)		28.5		dBm
Output Third Order Intercept (IP3) [2]	37	40		dBm
Noise Figure		8		dB
Supply Current (Icq)		310		mA
Control Current (Ipd)		12		mA
Switching Speed	tON, tOFF	10		ns

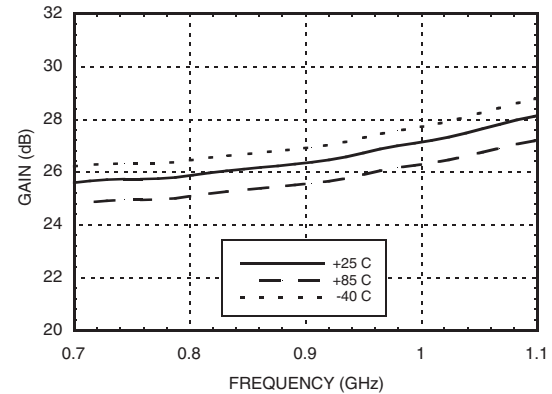
[1] Specifications and data reflect HMC450QS16G measured using the application circuit found herein. Contact the HMC Applications Group for assistance in optimizing performance for your application.

[2] Two-tone output power of +15 dBm per tone, 1 MHz spacing.

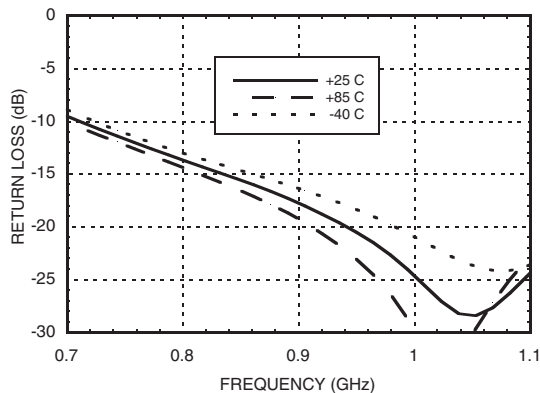
Broadband Gain & Return Loss



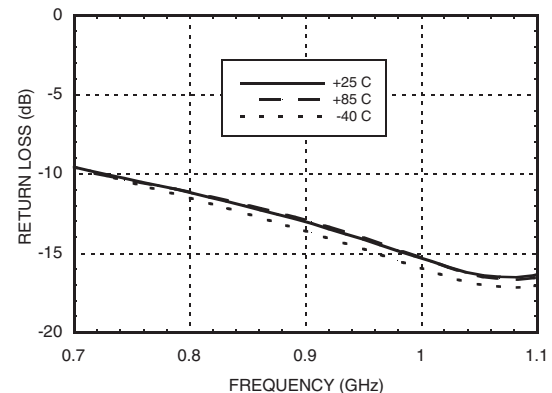
Gain vs. Temperature



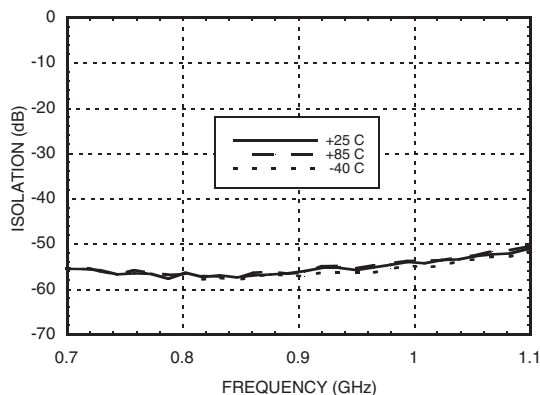
Input Return Loss vs. Temperature



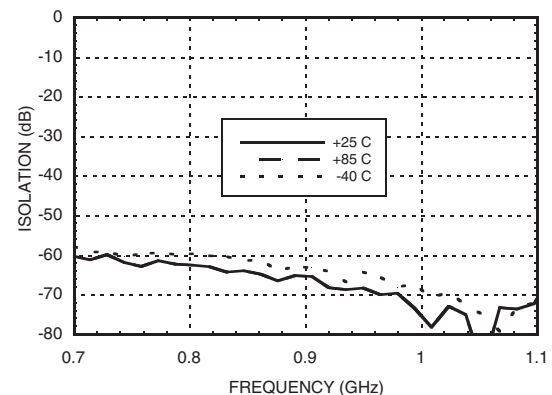
Output Return Loss vs. Temperature



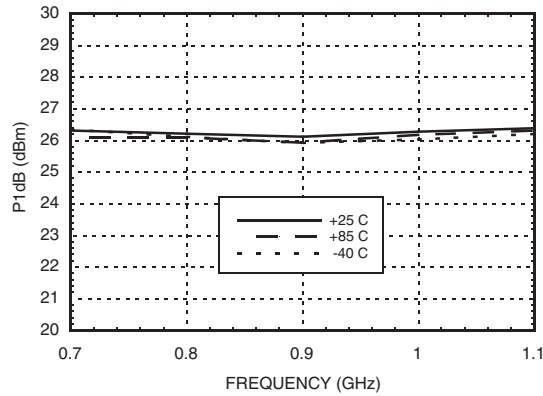
Reverse Isolation vs. Temperature



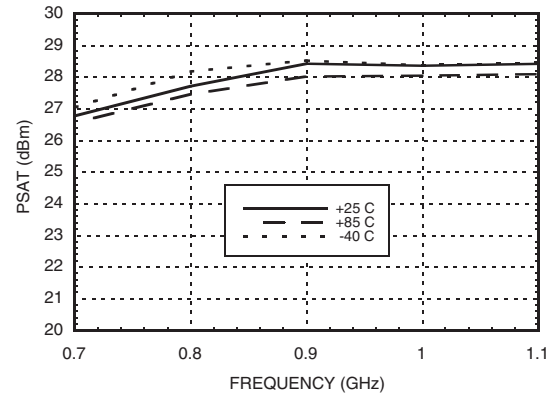
Power Down Isolation vs. Temperature



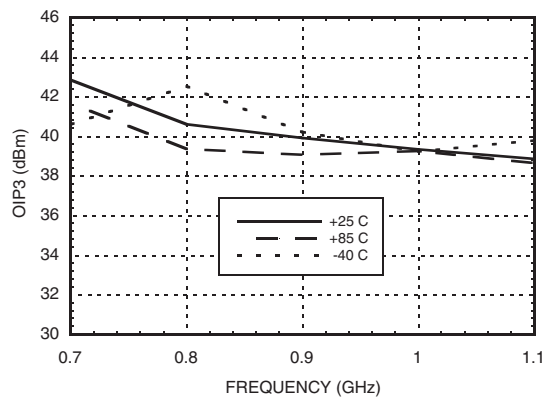
P1dB vs. Temperature



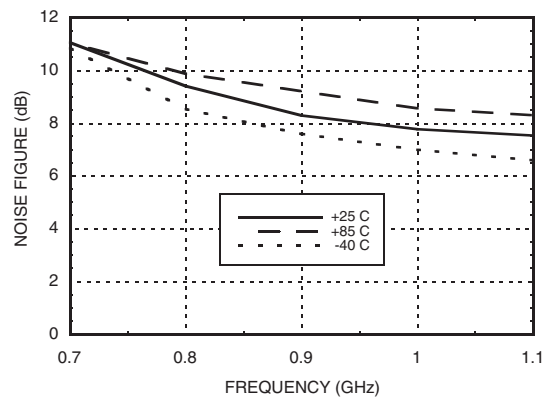
Psat vs. Temperature



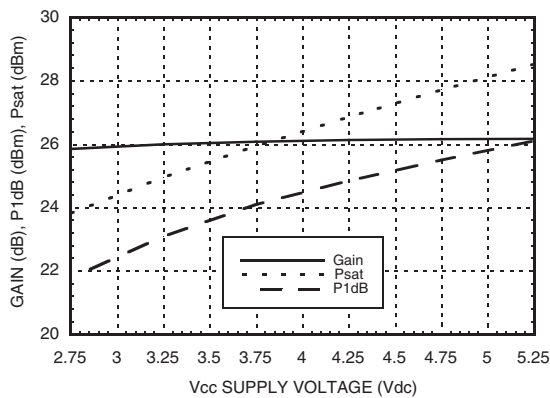
Output IP3 vs. Temperature



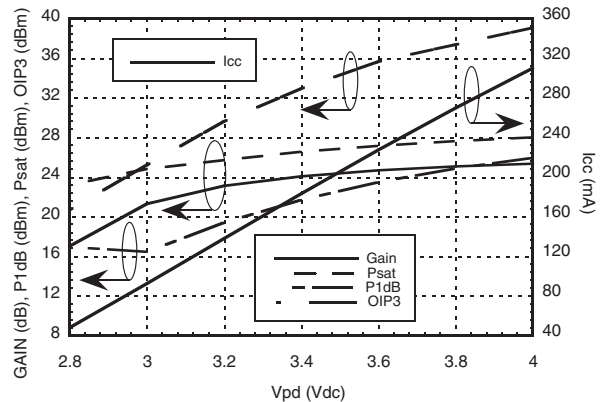
Noise Figure vs. Temperature



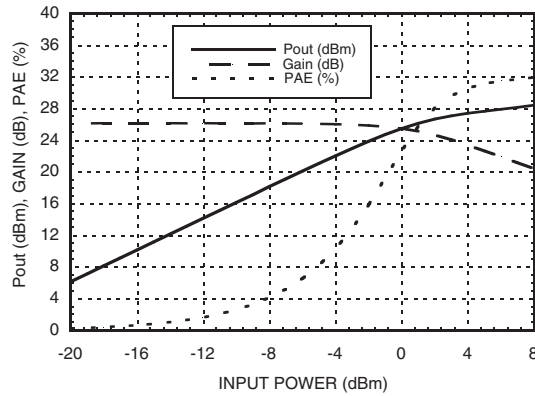
**Gain and Power vs.
Supply Voltage @ 900 MHz, Vpd= 4V**



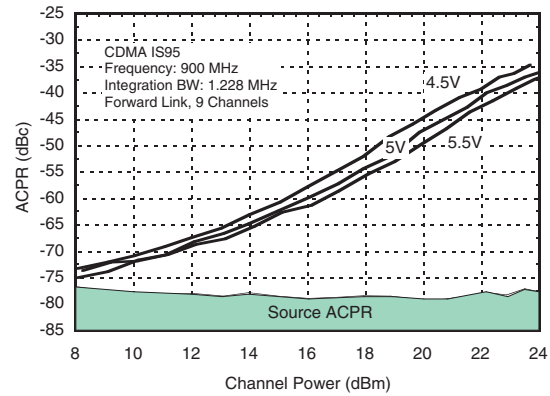
**Gain, Power, OIP3 and Supply Current
vs. Power Down Voltage @ 900 MHz**



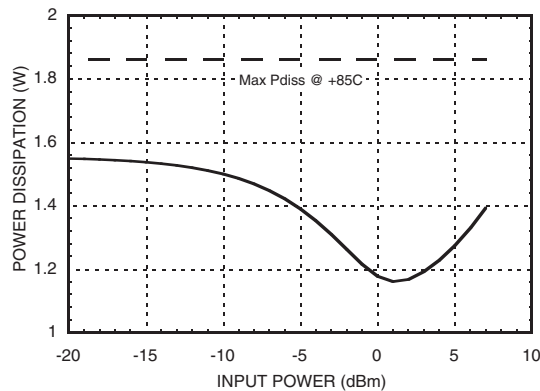
Power Compression @ 900 MHz



ACPR vs. Supply Voltage @ 900 MHz CDMA IS95, 9 Channels Forward



Power Dissipation @ 900 MHz



Absolute Maximum Ratings

Collector Bias Voltage (Vcc)	+5.5 Vdc
Control Voltage (Vpd1, Vpd2)	+5Vdc
RF Input Power (RFIN)(Vs = +5Vdc, VPD = +4.0 Vdc)	+10 dBm
Junction Temperature	150 °C
Continuous P _{diss} (T = 85 °C) (derate 28 mW/°C above 85 °C)	1.86 W
Thermal Resistance (junction to ground paddle)	35 °C/W
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C

Typical Supply Current vs. Supply Voltage

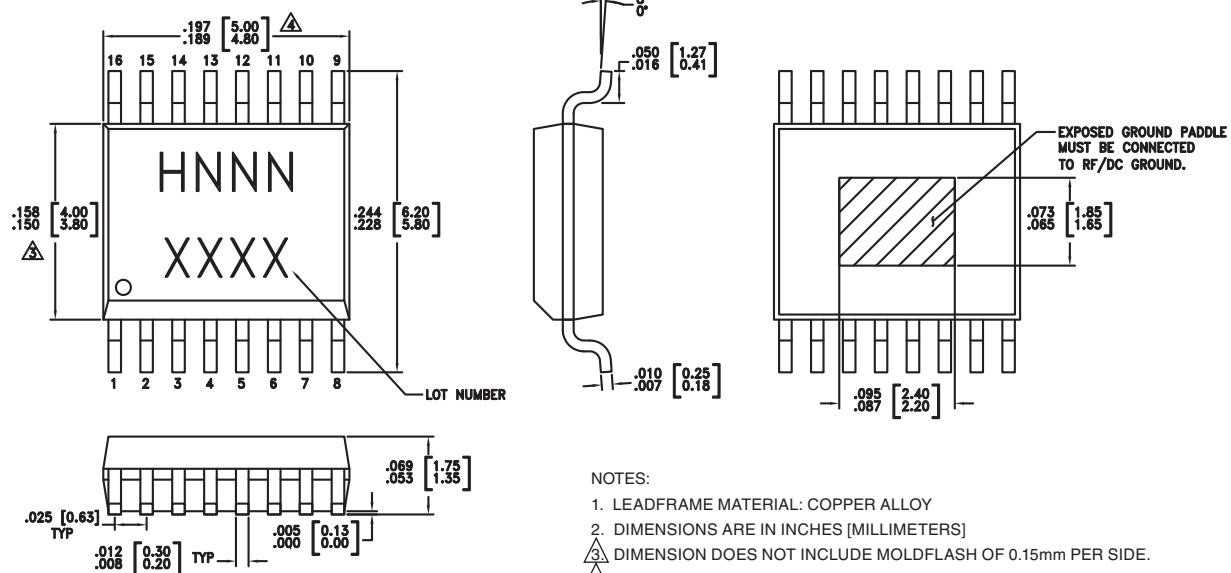
Vs (V)	Ic _q (mA)
4.75	300
5.0	310
5.25	325

Note: Amplifier will operate over full voltage range shown above



ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing



Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking ^[3]
HMC450QS16G	Low Stress Injection Molded Plastic	Sn/Pb Solder	MSL1 ^[1]	H450 XXXX
HMC450QS16GE	RoHS-compliant Low Stress Injection Molded Plastic	100% matte Sn	MSL1 ^[2]	H450 XXXX

[1] Max peak reflow temperature of 235 °C

[2] Max peak reflow temperature of 260 °C

[3] 4-Digit lot number XXXX

For price, delivery, and to place orders, please contact Hittite Microwave Corporation:
20 Alpha Road, Chelmsford, MA 01824 Phone: 978-250-3343 Fax: 978-250-3373
Order On-line at www.hittite.com



MICROWAVE CORPORATION

v02.0406



HMC450QS16G / 450QS16GE

GaAs InGaP HBT MMIC
POWER AMPLIFIER, 0.8 - 1.0 GHz

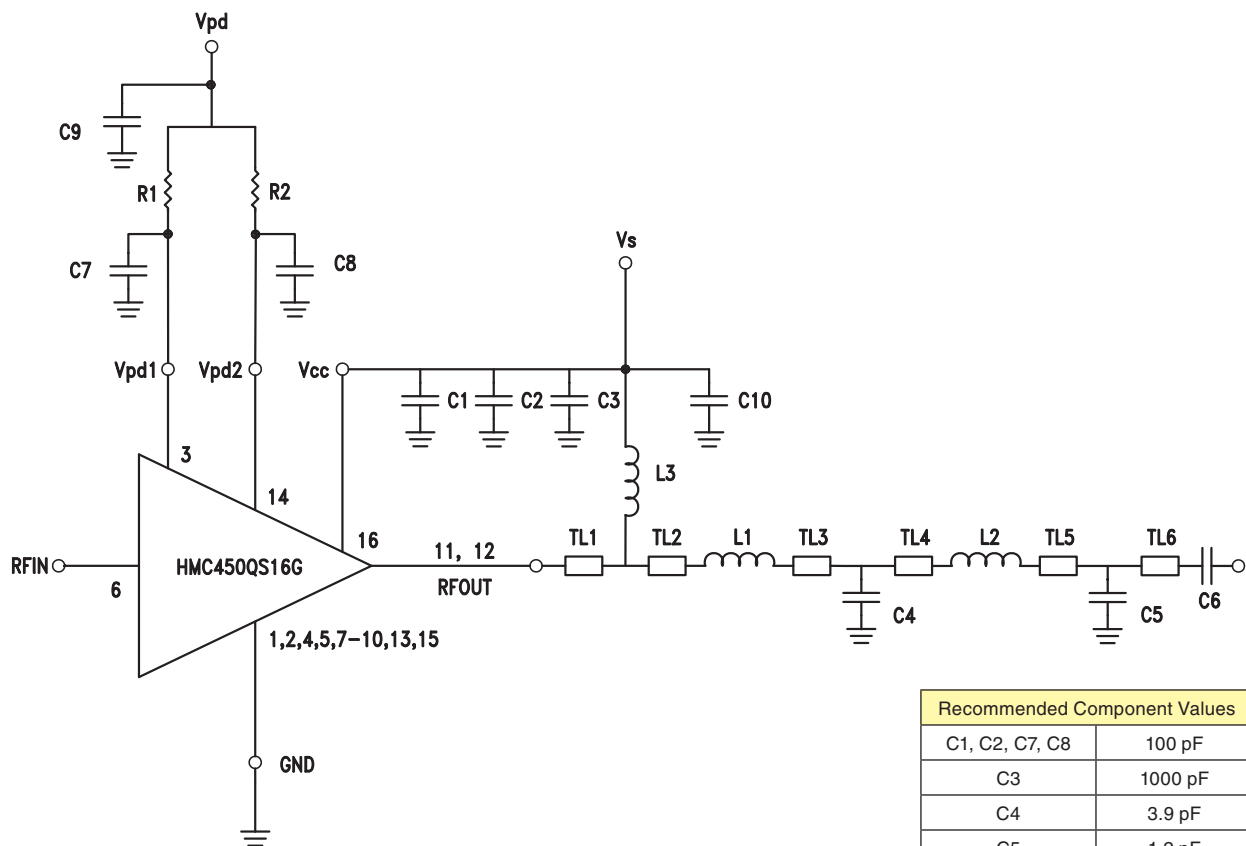
Pin Descriptions

Pin Number	Function	Description	Interface Schematic
1, 2, 4, 5, 7, 8, 9, 10, 13, 15	GND	Ground: Backside of package has exposed metal ground slug that must be connected to ground thru a short path. Vias under the device are required.	
3, 14	Vpd1, Vpd2	Power Control Pin. For maximum power, this pin should be connected to 4.0V. For 5V operation, a dropping resistor is required. A higher voltage is not recommended. For lower idle current, this voltage can be reduced.	
6	RFIN	This pin is AC coupled and matched to 50 Ohms from 0.8 to 1.0 GHz.	
11, 12	RFOUT	RF output and bias for the output stage.	
16	Vcc	Power supply voltage for the first amplifier stage. An external bypass capacitor of 330 pF is required as shown in the application schematic.	

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LINEAR & POWER AMPLIFIERS - SMT

Application Circuit

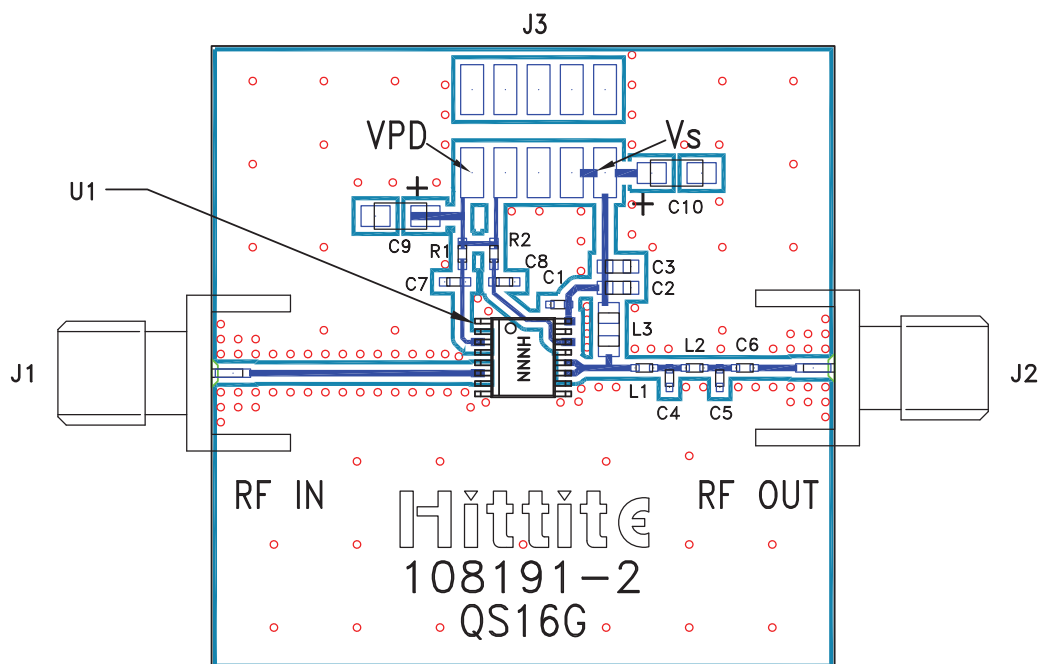


Recommended Component Values	
C1, C2, C7, C8	100 pF
C3	1000 pF
C4	3.9 pF
C5	1.2 pF
C6	27 pF
C9, C10	2.2 μ F
L1	1.9 nH
L2	1.0 nH
L3	56 nH
R1, R2	50 Ohms

		TL1	TL2	TL3	TL4	TL5	TL6
	Impedance	50 Ohm	50 Ohm	50 Ohm	50 Ohm	50 Ohm	50 Ohm
Physical	Length	0.08"	0.05"	0.02"	0.02"	0.02"	0.02"
Electrical	Length	4'	2.5'	1.02'	1.02'	1.02'	1.02'

PCB Material: 10 mil Rogers 4350 Er = 3.48

Evaluation PCB



List of Materials for Evaluation PCB 108349 ^[1]

Item	Description
J1 - J2	PCB Mount SMA Connector
J3	2 mm DC Header
C1, C7, C8	100 pF Capacitor, 0402 Pkg.
C2	100 pF Capacitor, 0603 Pkg.
C3	1000 pF Capacitor, 0603 Pkg.
C4	3.9 pF Capacitor, 0402 Pkg.
C5	1.2 pF Capacitor, 0402 Pkg.
C6	27 pF Capacitor, 0402 Pkg.
C9, C10	2.2 uF Capacitor, Tantalum
L1	1.9 nH Inductor 0402 Pkg.
L2	1.0 nH Inductor, 0402 Pkg.
L3	56nH Inductor, 0805 Pkg.
R1, R2	50 Ohms Resistor, 0402 Pkg.
U1	HMC450QS16G / HMC450QS16GE Power Amp.
PCB ^[2]	108191 Evaluation PCB, 10 mils

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the final application should use RF circuit design techniques. Signal lines should have 50 ohm impedance while the package ground leads and exposed paddle should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Hittite upon request.